SKN 5

Stud Diode

Rectifier Diode

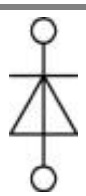
SKN 5

Features

- Reverse voltages up to 1600 V
- Hermetic metal case with glass insulator
- Anode side threaded stud ISO M4
- SKN: anode to stud
- With integrated cooling fins

Typical Applications

- All-purpose rectifier diodes
- For severe ambient conditions
- Recommended snubber network: RC: 0,02 µF, 500 Ω (P_R = 1 W) R_P = 270 kΩ (P_R = 2 W)



SKN

V_{RSM} V	V_{RRM} V	I_{FRMS} = 10 A (maximum value for continuous operation) I_{FAV} = 5 A (sin. 180; T_a = 45 °C)		
200	200	SKN 5/02		
400	400	SKN 5/04		
800	800	SKN 5/08		
1200	1200	SKN 5/12		
1600	1600	SKN 5/16		

Symbol	Conditions	Values	Units
I_{FAV}	sin. 180; T_a = 45 °C	5	A
I_{FSM}	T_{vj} = 25 °C; 10 ms	190	A
	T_{vj} = 180 °C; 10 ms	160	A
i²t	T_{vj} = 25 °C; 8,3 ... 10 ms	180	A²s
	T_{vj} = 180 °C; 8,3 ... 10 ms	130	A²s
V_F	T_{vj} = 25 °C; I_F = 15 A	max. 1,25	V
$V_{(TO)}$	T_{vj} = 180 °C	max. 0,85	V
r_T	T_{vj} = 180 °C	max. 25	mΩ
I_{RD}	T_{vj} = 180 °C; V_{RD} = V_{RRM}	max. 2,2	mA
Q_{rr}	T_{vj} = 160 °C; - di_F/dt = 10 A/µs	18	µC
$R_{th(j-c)}$		1,8	K/W
$R_{th(j-a)}$		25	K/W
T_{vj}		- 40 ... + 180	°C
T_{stg}		- 55 ... + 180	°C
V_{isol}		-	V~
M_s	to heatsink	0,8	Nm
a		5 * 9,81	m/s²
m	approx.	20	g
Case		E 6	

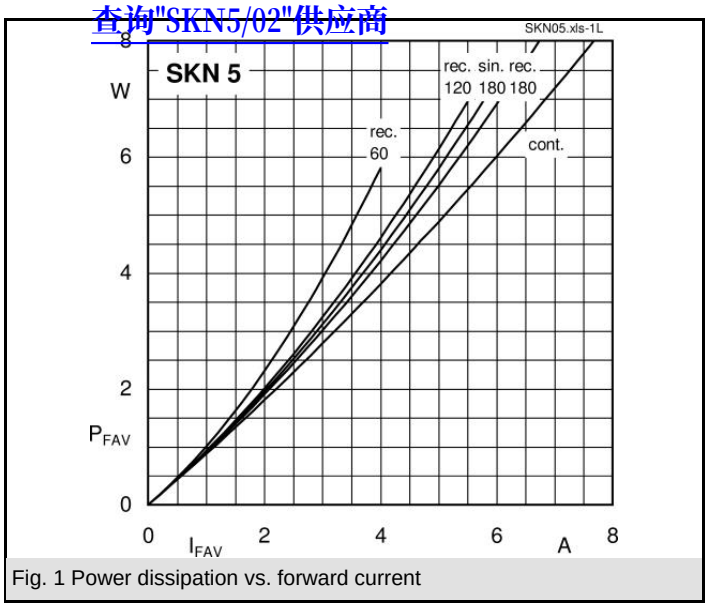


Fig. 1 Power dissipation vs. forward current

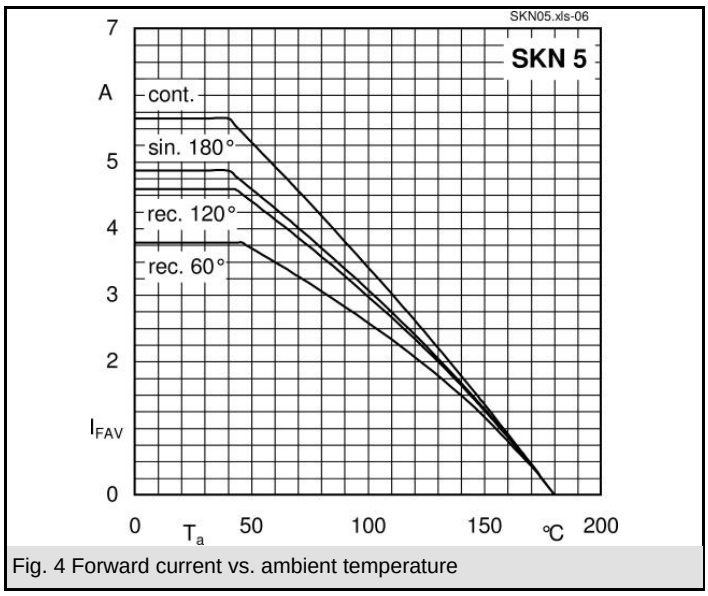


Fig. 4 Forward current vs. ambient temperature

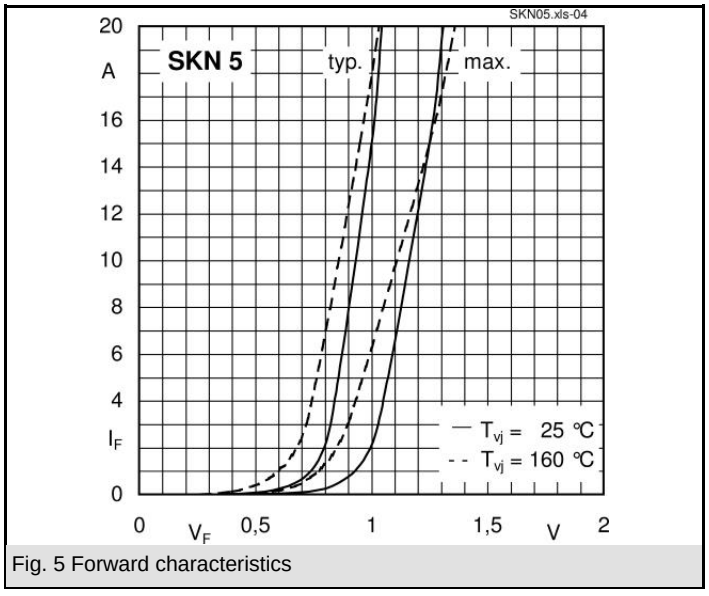


Fig. 5 Forward characteristics

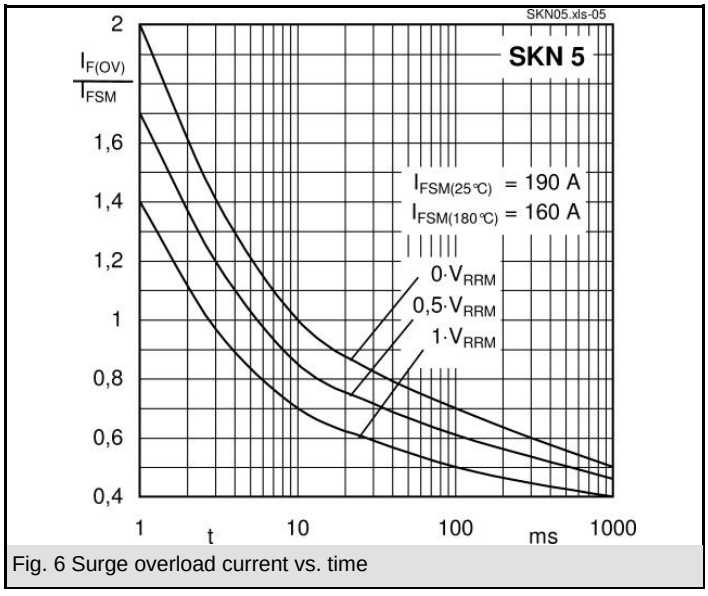


Fig. 6 Surge overload current vs. time

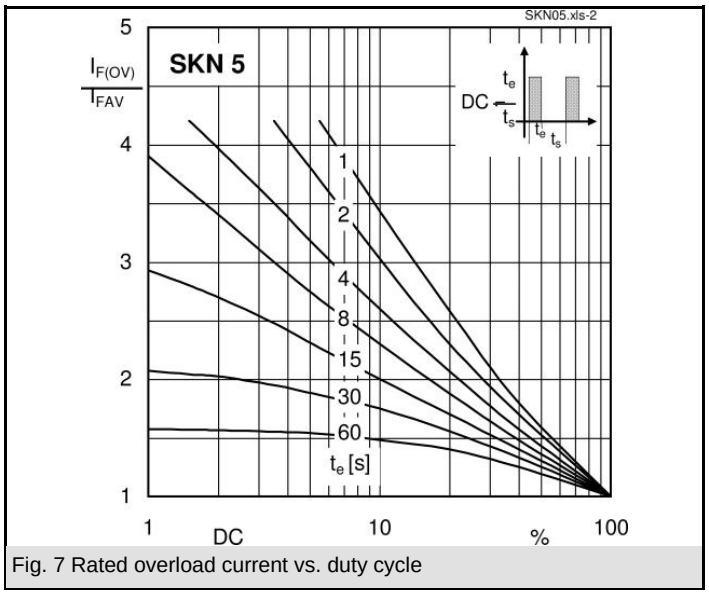


Fig. 7 Rated overload current vs. duty cycle

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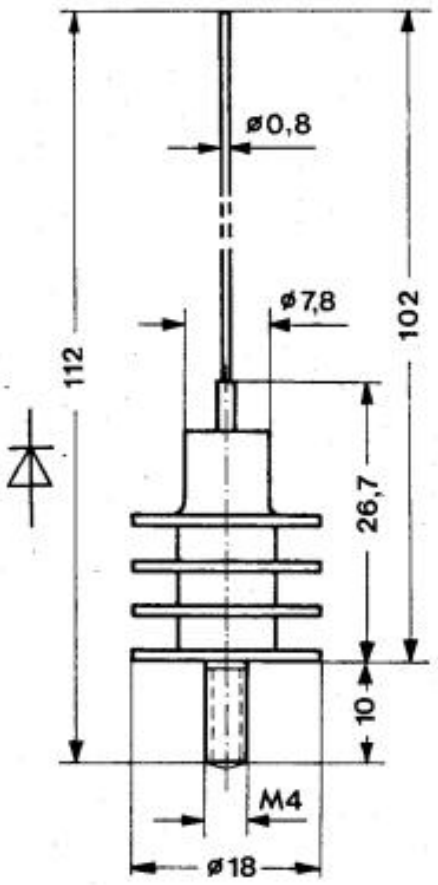
Dimensions in mm



Case E 6

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